

Silicon NPN Power Transistor

MJE243

DESCRIPTION

- Collector–Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 100\text{ V}(\text{Min})$
- DC Current Gain-
: $h_{FE} = 40(\text{Min}) @ I_C = 0.2\text{ A}$
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = 0.3\text{V}(\text{Max.}) @ I_C = 0.5\text{ A}$
- Complement to Type MJE253

APPLICATIONS

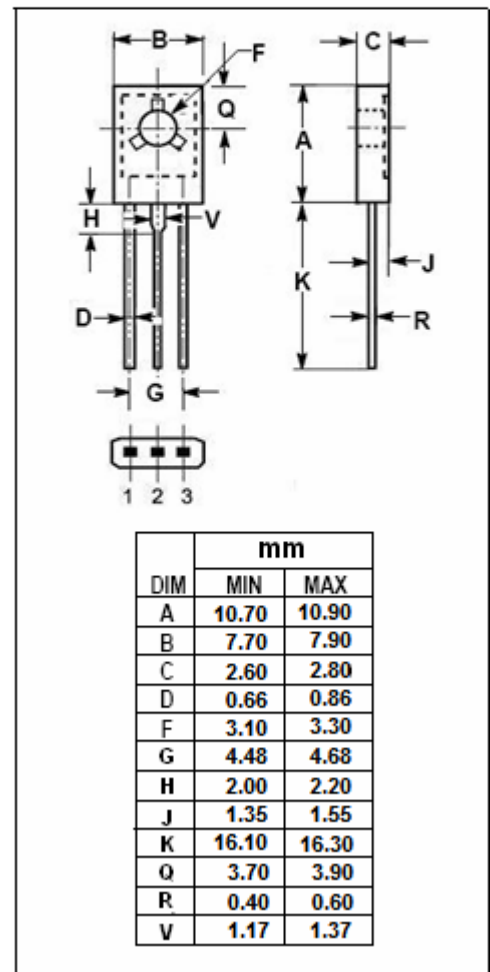
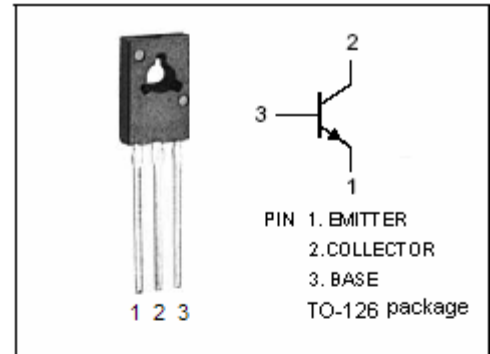
- Designed for low power audio amplifier and low-current, high-speed switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Collector Current-Peak	8	A
I_B	Base Current	1	A
P_C	Collector Power Dissipation $T_a=25$	1.5	W
	Collector Power Dissipation $T_C=25$	15	
T_j	Junction Temperature	150	
T_{stg}	Storage Temperature Range	-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	8.34	/W
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	83.4	/W



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ELECTRICAL CHARACTERISTICS

 $T_C = 25$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = 10mA; I_B = 0$	100		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = 0.5 A; I_B = 50mA$		0.3	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = 1A; I_B = 0.1A$		0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 2A; I_B = 0.2A$		1.8	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 0.5A; V_{CE} = 1V$		1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 100V; I_E = 0$ $V_{CB} = 100V; I_E = 0; T_C = 125$		0.1 0.1	μA mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 7V; I_C = 0$		0.1	μA
h_{FE-1}	DC Current Gain	$I_C = 0.2 A; V_{CE} = 1V$	40	180	
h_{FE-2}	DC Current Gain	$I_C = 1A; V_{CE} = 1V$	15		
f_T	Current-Gain—Bandwidth Product	$I_C = 0.1 A; V_{CE} = 10V; f_{test} = 10MHz$	40		MHz
C_{OB}	Collector Capacitance	$I_E = 0; V_{CB} = 10V; f_{test} = 0.1MHz$		50	pF